

MICRO ELECTRONICS

BFR79

PNP
SILICON
TRANSISTOR

BFR79 is PNP silicon planar transistor designed for medium power applications.

TO-92B



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	80V
Collector-Base Voltage	V _{CBO}	90V
Emitter-Base Voltage	V _{EBO}	5V
Total Power Dissipation	P _{tot}	800mW
Collector Current	I _C	1A
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CEO}	80		V	I _C =10mA I _B =0
Collector-Base Breakdown Voltage	BV _{CBO}	90		V	I _C =100μA I _E =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5		V	I _E =100μA I _C =0
Collector Cutoff Current	I _{CBO}		100	nA	V _{CB} =80V I _E =0
D.C. Current Gain	H _{FE}	50 20			I _C =100mA V _{CE} =10V* I _C =1A V _{CE} =10V*
Collector-Emitter Saturation Voltage	V _{CE(sat)}		1.6	V	I _C =1A I _B =0.1A*
Base-Emitter Saturation Voltage	V _{BE(sat)}		2.0	V	I _C =1A I _B =0.1A*
Current Gain Bandwidth Product	f _T	100	TYP	MHz	I _C =40mA V _{CE} =10V f=20MHz
Output Capacitance	C _{ob}	12	TYP	pF	V _{CB} =10V f=1MHz

* Pulse Test : Pulse Width <300us, duty cycle <2%.



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